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(54) Title: APPARATUS AND METHODS FOR PREDICTING A SEMICONDUCTOR PARAMETER ACROSS AN AREA OF A WAFER

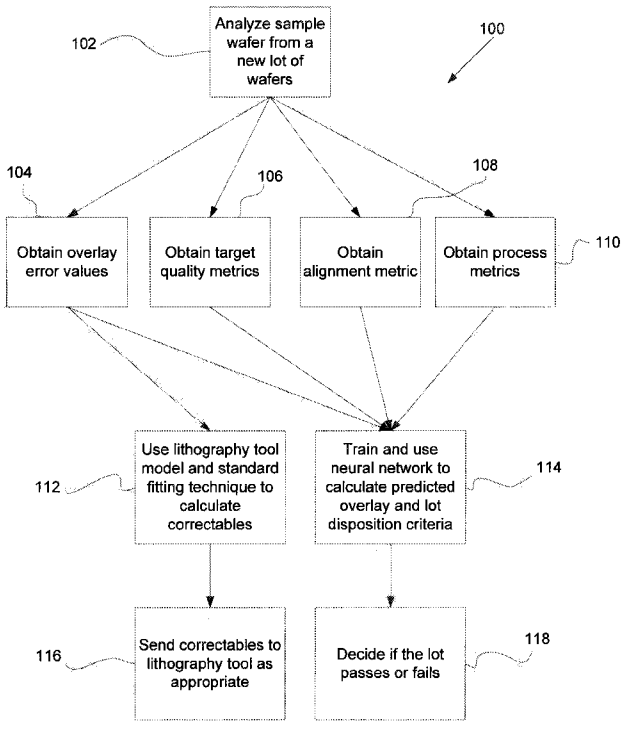


FIG. 1

(57) Abstract: Apparatus and methods are provided for predicting a plurality of unknown parameter values (e.g. overlay error or critical dimension) using a plurality of known parameter values. In one embodiment, the method involves training a neural network to predict the plurality of parameter values (114, 700, 800, 900). In other embodiments, the prediction process does not depend on an optical property of a photolithography tool. Such predictions may be used to determine wafer lot disposition (114).

WO 2009/029851 A3

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